

1-Line Uni-directional TVS Diode

Description

The PESDU4851P1 is an uni-directional TVS diode, utilizing leading monolithic silicon technology to provide fast response time and low ESD clamping voltage, making this device an ideal solution for protecting voltage sensitive data and power line. The PESDU4851P1 complies with the IEC 61000-4-2 (ESD) with ±30kV air and ±30kV contact discharge. It is assembled into an ultra-small 1.0x0.6x0.5mm lead-free DFN package. The small size and high ESD surge protection make PESDU4851P1 an ideal choice to protect cell phone, digital cameras, audio players and many other portable applications.

Features

- Ultra small package: 1.0x0.6x0.5mm
- · Protects one data or power line
- Operating voltage: 4.8V
- Low clamping voltage
- 2-Pin leadless package
- · Complies with following standards:
 - IEC 61000-4-2 (ESD) immunity test

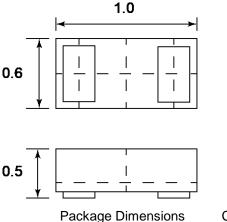
Air discharge: ±30kV

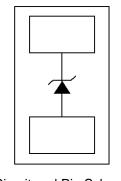
Contact discharge: ±30kV

- IEC61000-4-5 (Lightning) 40A (8/20µs)

RoHS Compliant

Dimensions and Pin Configuration





Circuit and Pin Schematic

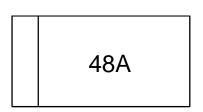
Mechanical Characteristics

- Package: DFN1006-2 (1.0×0.6×0.5mm)
- Case Material: "Green" Molding Compound.
- Moisture Sensitivity: Level 1 per J-STD-020
- Marking Information: See Below

Applications

- Cellular Handsets and Accessories
- Personal Digital Assistants
- Notebooks and Handhelds
- Portable Instrumentation
- Digital Cameras
- Peripherals
- Audio Players
- Keypads, Side Keys, LCD Displays

Marking Information



48A = Device Marking Code Bar denotes cathode

Ordering Information

P	art Number	Shipping	Reel Size
PE	ESDU4851P1	10000/Tape & Reel	7 inch



Absolute Maximum Ratings (TA=25°C unless otherwise specified)

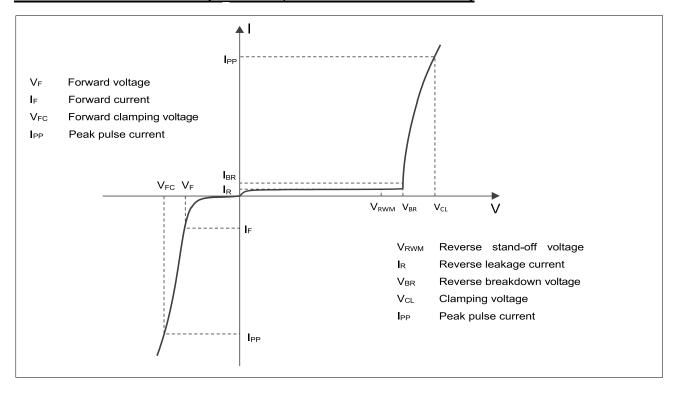
Parameter	Symbol	Value	Unit		
Peak Pulse Power (8/20μs)	Ррк	560	W		
Peak Pulse Current (8/20µs)	I _{PP}	40	А		
ESD per IEC 61000-4-2 (Air)	V	±30	127		
ESD per IEC 61000-4-2 (Contact)	V _{ESD}	±30	- kV		
Lead temperature	TL	260	°C		
Operating Temperature Range	Тор	-40 ~ + 85	°C		
Storage Temperature Range	Тѕтс	−55 ~ + 150	°C		

Electrical Characteristics (TA=25°C unless otherwise specified)

Parameter	Symbol	Min	Тур	Max	Unit	Test Condition
Reverse Working Voltage	V _{RWM}			4.8	V	
Breakdown Voltage	V_{BR}	6			V	$I_T = 1mA$
Reverse Leakage Current	I _R			1	μA	V _{RWM} = 5V
Forward Voltage	VF			1.1	V	I _F = 10mA
Clamping Voltage	Vc			9	V	I _{PP} = 5A (8/20μs pulse)
Clamping Voltage	Vc			14	V	I _{PP} = 40A (8/20µs pulse)
Junction Capacitance	Сл		260		pF	V _R = 0V, f = 1MHz



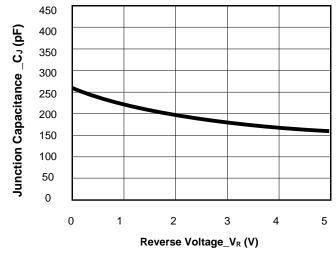
Electrical characteristics (T_A = 25°C, unless otherwise noted)



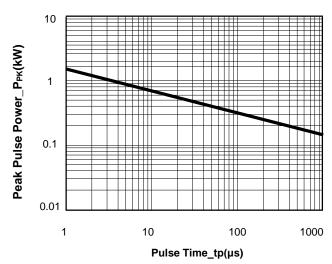
Definitions of electrical characteristics



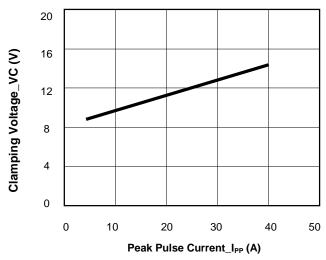
Typical Performance Characteristics (T_A=25°C unless otherwise Specified)



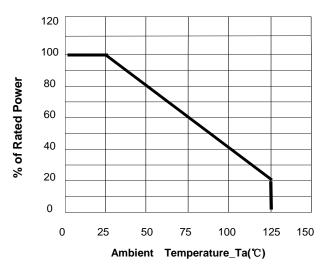
Junction Capacitance vs. Reverse Voltage



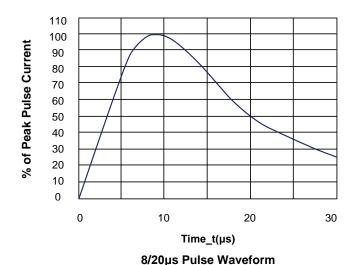
Peak Pulse Power vs. Pulse Time



Clamping Voltage vs. Peak Pulse Current

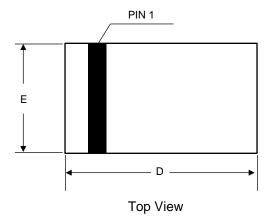


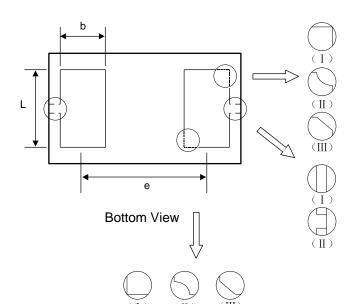
Power Derating Curve

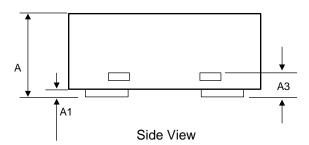




DFN1006-2 Package Outline Drawing

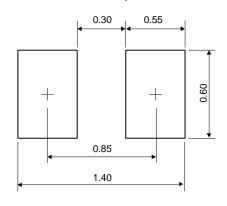






Cumbal		Dimensions in Millimeters			
Symbol	Min.	Тур.	Max.		
А	0.340	0.450	0.550		
A1	0.000	0.020	0.050		
А3		0.125 Ref.			
D	0.950	1.000	1.075		
E	0.490	0.600	0.675		
b	0.200	0.250	0.300		
L	0.450	0.500	0.550		
е		0.650 BSC			

Recommended PCB Layout (Unit: mm)



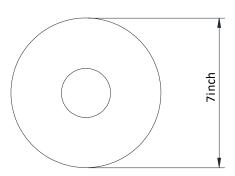
Notes:

This recommended land pattern is for reference purposes only. Please consult your manufacturing group to ensure your PCB design guidelines are met.

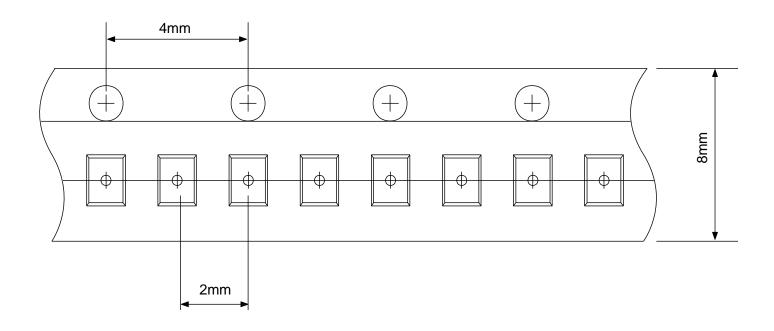


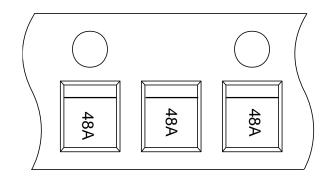
TAPE AND REEL INFORMATION





Tape Dimensions







User Direction of Feed



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